

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| L1 | 6 | ("RIE" near4 photoresist) same remov\$4 and (low near8 angle) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 08:20 |
| L2 | 7 | ((("RIE" or "reactive ion etching") near4 photoresist) same remov\$4 and (low near8 angle) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 08:21 |
| L4 | 16 | (ion near etch\$4) same "low angle" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 09:56 |
| L5 | 7 | (ion near etch\$4) same "low angle" and RIE | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 10:01 |
| L6 | 1 | (ion near etch\$4) same "low angle" and RIE and (remain\$4 near photoresist) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 09:59 |
| L7 | 1 | (ion near etch\$4) same "low angle" and RIE and (remain\$4 near8 photoresist) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 10:00 |
| L8 | 2 | (ion near etch\$4) same "low angle" and RIE and photoresist and mask and remov\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 10:00 |
| L9 | 1 | (ion near etch\$4) same "low angle" and RIE and photoresist and mask and remov\$4 and dielectric | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 10:00 |

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|-----|---|--|---|----|----|------------------|
| L10 | 6 | (ion near etch\$4) same "low angle" and RIE and dielectric | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 10:05 |
| L11 | 1 | (ion near etch\$4) same "low angle" and RIE and dielectric and photoresist | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 10:01 |
| L12 | 2 | (ion near etch\$4) same (low adj angle) and RIE and photoresist | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/09/16 10:05 |